MCR8M, MCR8N

Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half–wave, silicon gate–controlled devices are needed.

- Blocking Voltage of 600 thru 800 Volts
- On–State Current Rating of 8 Amperes RMS at 80°C
- High Surge Current Capability — 80 Amperes
- Rugged, Economical TO220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- High Immunity to dv/dt — 100 V/μsec Minimum at 125°C
- Device Marking: Logo, Device Type, e.g., MCR8N, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

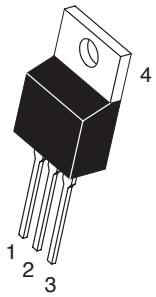
Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage(1) (T_J = –40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR8M MCR8N	V_{DRM}, V_{RRM}	600 800	Volts
On-State RMS Current (180° Conduction Angles; T_C = 80°C)	$I_{T(RMS)}$	8.0	Amps
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T_C = 125°C)	I_{TSM}	80	Amps
Circuit Fusing Consideration (t = 8.33 ms)	I^2t	26.5	A^2sec
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T_C = 80°C)	P_{GM}	5.0	Watts
Forward Average Gate Power (t = 8.3 ms, T_C = 80°C)	$P_{G(AV)}$	0.5	Watt
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T_C = 80°C)	I_{GM}	2.0	Amps
Operating Junction Temperature Range	T_J	–40 to 125	°C
Storage Temperature Range	T_{stg}	–40 to 150	°C

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

ON Semiconductor

http://onsemi.com

SCRs
8 AMPERES RMS
600 thru 800 VOLTS



TO–220AB
CASE 221A
STYLE 3

PIN ASSIGNMENT	
1	Cathode
2	Anode
3	Gate
4	Anode

ORDERING INFORMATION

Device	Package	Shipping
MCR8M	TO220AB	50 Units/Rail
MCR8N	TO220AB	50 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

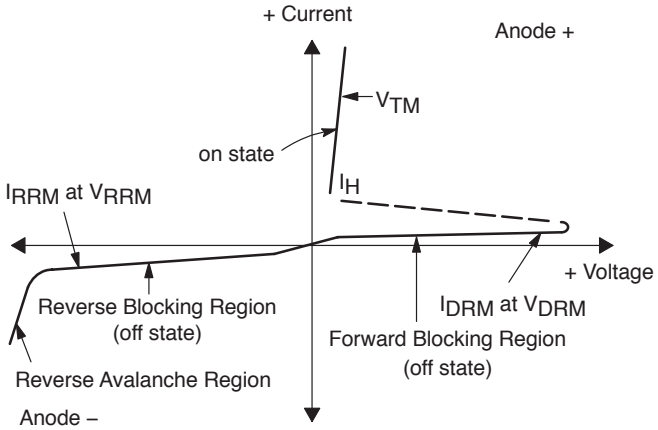
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current (V_D = Rated V_{DRM} and V_{RRM}; Gate Open)	 T_J = 25°C T_J = 125°C	I_{DRM}, I_{RRM}	 — —	 — —	 0.01 2.0	mA
ON CHARACTERISTICS						
Peak Forward On–State Voltage* (I_{TM} = 16 A)		V_{TM}	—	—	1.8	Volts
Gate Trigger Current (Continuous dc) (V_D = 12 V; R_L = 100 Ω)		I_{GT}	2.0	7.0	15	mA
Holding Current (V_D = 12 V, Gate Open, Initiating Current = 200 mA)		I_H	4.0	17	30	mA
Latch Current (V_D = 12 V, I_G = 15 mA)		I_L	6.0	20	40	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V; 100 Ω)	T_J = 25°C	V_{GT}	0.5	0.65	1.0	Volts
Gate Non–Trigger Voltage (V_D = 12 V; R_L = 100 Ω)	T_J = 125°C	V_{GD}	0.2	—	—	Volts
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage (V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)		dv/dt	100	250	—	V/μs
Critical Rate of Rise of On–State Current IPK = 50 A, Pw = 40 μsec, diG/dt = 1 A/μsec, Igt = 50 mA		di/dt	—	—	50	A/μs

*Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current



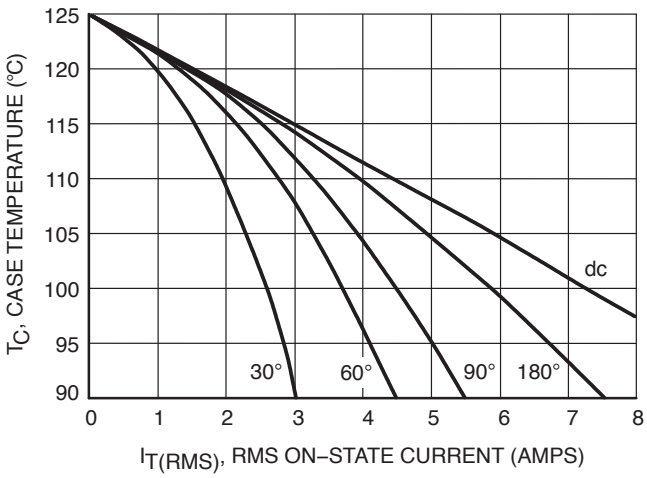


Figure 1. Typical RMS Current Derating

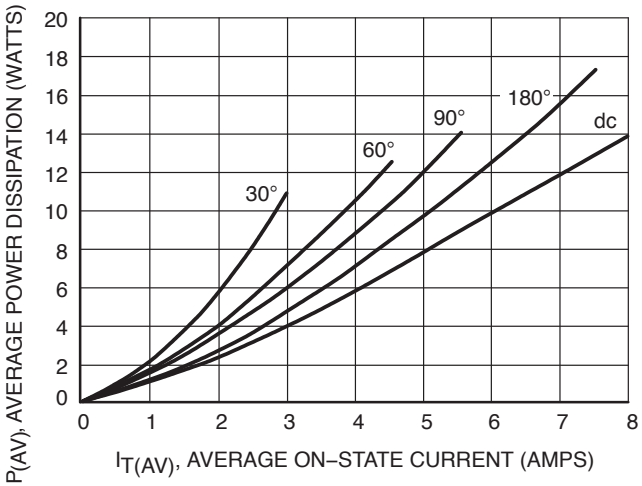


Figure 2. On–State Power Dissipation

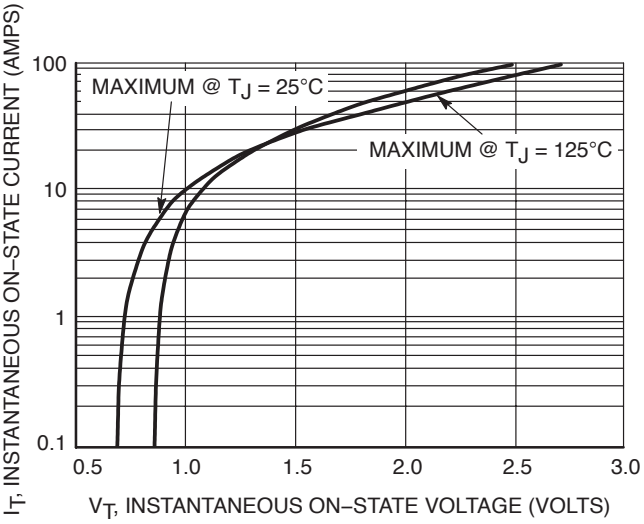


Figure 3. Typical On–State Characteristics

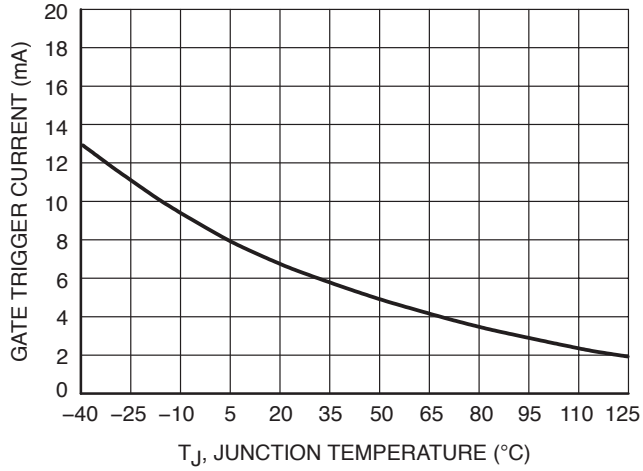


Figure 4. Typical Gate Trigger Current versus Junction Temperature

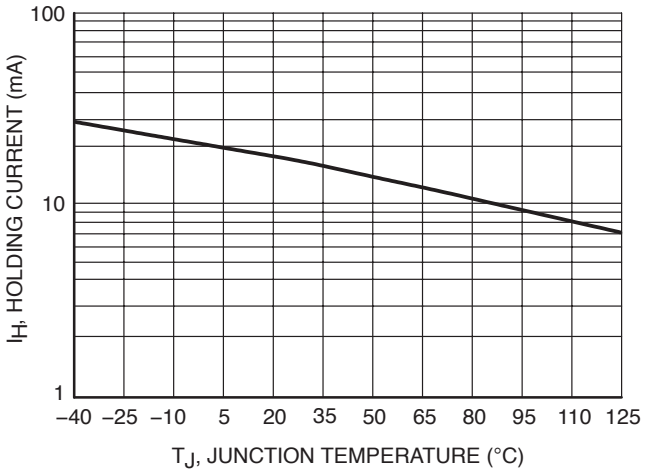


Figure 5. Typical Holding Current versus Junction Temperature

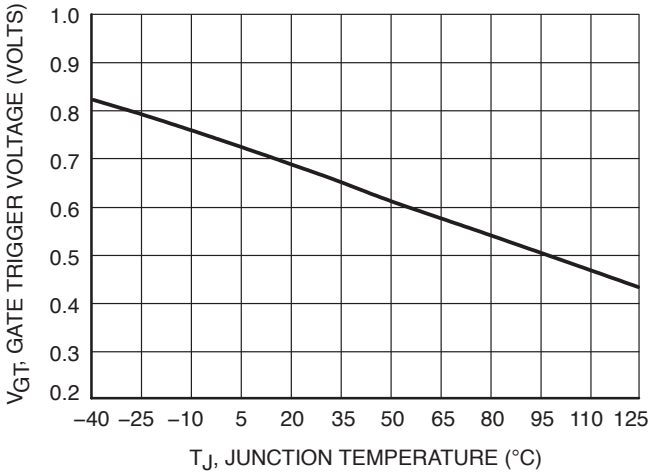


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

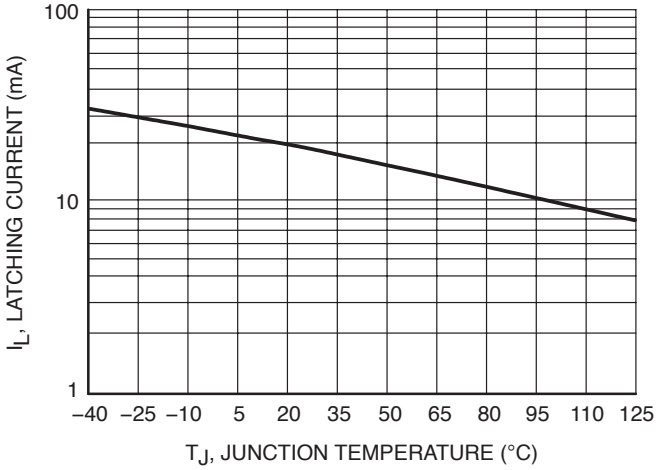


Figure 7. Typical Latching Current versus Junction Temperature